

Si Photo-diode Chip—TK0N55PDN

1. Scope

- The specification applies to NIP silicon photo-diode chips.
- Type : TK0N55PDN

2. Structure

- PIN planar type.
- Electrode topside (cathode) : Aluminum.
backside (anode) : Gold alloy.

3. Size

- Chip size : 55mil×55mil , ±2mil (1.397mm×1.397mm , ±0.050mm)
- Thickness : 12mil , ±1mil (0.300mm , ±0.025mm)
- Active area : 48mil×48mil , ±0.5mil (1.2192mm×1.2192mm , ±0.013mm)
- Pattern drawing : per fig. 2

4. Electro-Optical Characteristics

T_a = +25 °C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit.
Forward Voltage	V _F	I _F =10mA, H=0	0.5		1.3	V
Reverse Breakdown Voltage	V _{BR}	I _R =100μA, H=0	35			V
Reverse Dark Current	I _D	V _R =10 V, H=0			10	nA
Light Current	I _L	V _R =5 V, H as 1 mw/cm ² @940nm		52		μA
Peak Sensing Wavelength	λ _p			940		nm
Junction Capacitance	C _J	V _R =3 V, H=0, F=1 MHz		3		pF

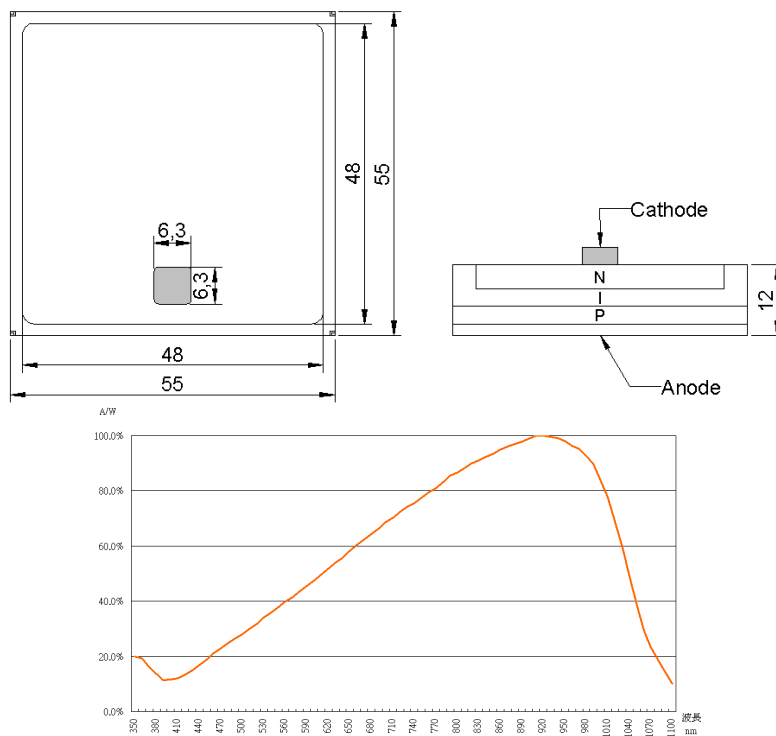


Fig. 1



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